

In the Claims

34 64. (currently amended) An intermediate construction of an integrated circuit comprising:

- a) a semiconductive substrate;
- b) a raised mandril over the substrate, the raised mandril being raised out from the substrate and having at least one edge substantially perpendicular to the substrate and having at least one beveled edge; and
- c) a layer of structural material forming an edge defined feature on the at least one perpendicular edge.

65. (currently amended) The ~~method~~ construction of claim 64, wherein the bevel is less than or equal to about 45°.

66. (currently amended) The ~~method~~ construction of claim 64, wherein the raised mandril comprises four edges, including two edges substantially perpendicular to the substrate and two beveled edges.

67. (currently amended) The ~~method~~ construction of claim 64, wherein the structural material is conductive.

35 68. (new) The construction of claim 64, further comprising a step at the at least one perpendicular edge from the substrate to the raised mandril.

B⁵ 69. (new) The construction of claim 66, further comprising a step at each of the four edges from the substrate to the raised mandril.

70. (new) The construction of claim 64, wherein the structural material layer comprises a substantially uniformly thick layer.

71. (new) An intermediate construction of an integrated circuit comprising:

a) a semiconductive substrate;

b) a raised mandril over the substrate, the raised mandril being raised out from the substrate and having at least one edge substantially perpendicular to the substrate, at least one beveled edge, and a step parallel to the substrate; and

c) a layer of structural material forming an edge defined feature on the at least one perpendicular edge, but not on the beveled edge or the step.

72. (new) The construction of claim 71, wherein the edge defined feature extends to a full lateral extent of the perpendicular edge.

73. (new) The construction of claim 71, wherein the edge defined feature extends to a full vertical extent of the perpendicular edge.

74. (new) The construction of claim 71, wherein the bevel is less than or equal to about 45°.

75. (new) The construction of claim 71, wherein the raised mandril comprises four edges, including two edges substantially perpendicular to the substrate and two beveled edges.

85 76. (new) The construction of claim 71, wherein the structural material is conductive.

77. (new) The construction of claim 71, further comprising a step at the at least one perpendicular edge from the substrate to the raised mandril.

78. (new) The construction of claim 75, further comprising a step at each of the four edges from the substrate to the raised mandril.

79. (new) The construction of claim 71, wherein the edge defined feature comprises a substantially uniformly thick layer.

80. (new) An intermediate construction of an integrated circuit comprising:

a) a semiconductive substrate;

b) a raised mandril over the substrate, the raised mandril being raised out from the substrate and having at least one edge substantially perpendicular to the substrate and at least one beveled edge; and

c) a layer of structural material forming an edge defined feature on the at least one perpendicular edge, the edge defined feature extending to a full lateral extent of the perpendicular edge.

81. (new) The construction of claim 80, wherein the edge defined feature extends to a full vertical extent of the perpendicular edge.

82. (new) The construction of claim 80, wherein the bevel is less than or equal to about 45°.

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83. (new) The construction of claim 80, wherein the raised mandril comprises four edges, including two edges substantially perpendicular to the substrate and two beveled edges.

84. (new) The construction of claim 80, wherein the structural material is conductive.

85. (new) The construction of claim 80, further comprising a step at the at least one perpendicular edge from the substrate to the raised mandril.

86. (new) The construction of claim 83, further comprising a step at each of the four edges from the substrate to the raised mandril.

87. (new) The construction of claim 80, wherein the edge defined feature comprises a substantially uniformly thick layer.
